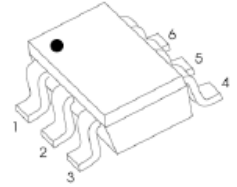
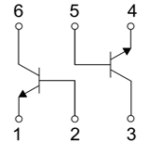


BC817DS

BC817DS DUAL TRANSISTOR (NPN+NPN)

FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors



MARKING: 6Bs

SOT23- 6L

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

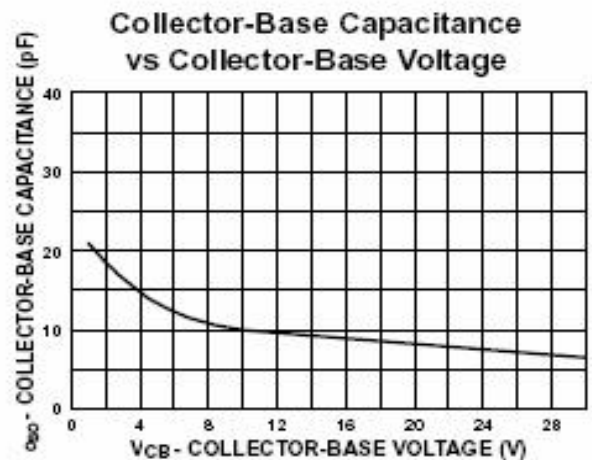
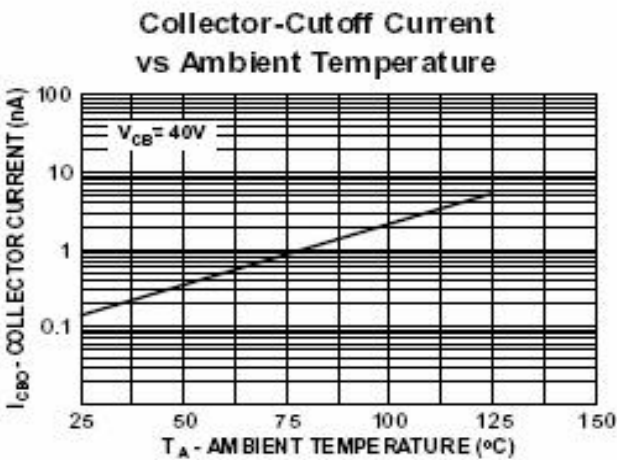
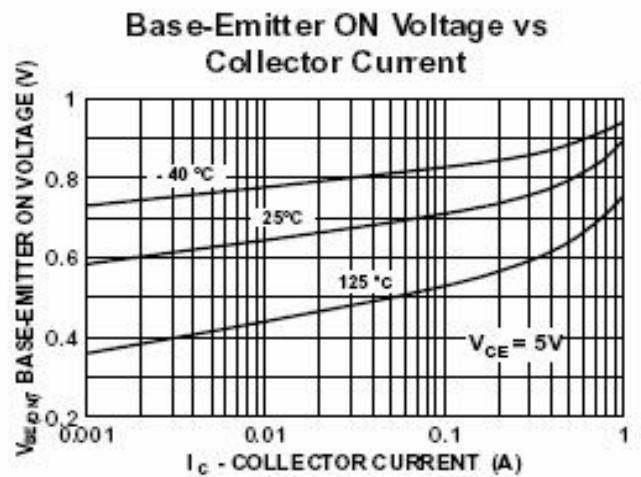
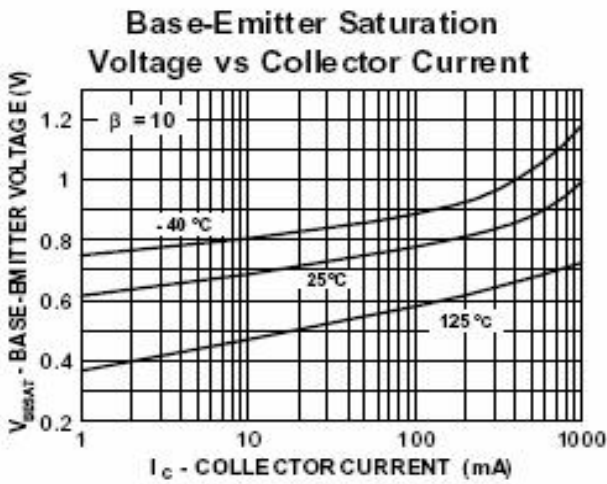
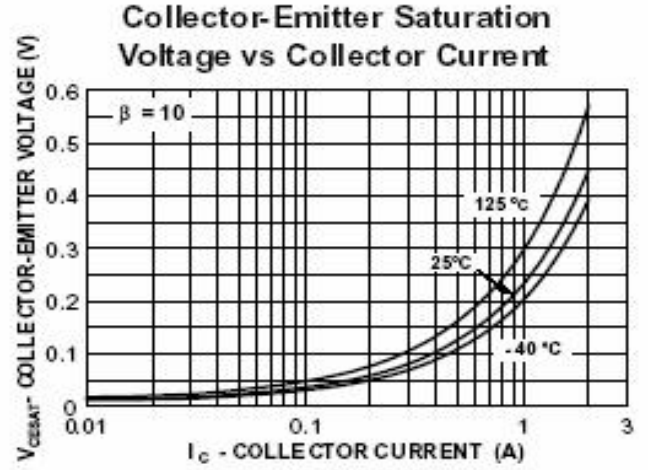
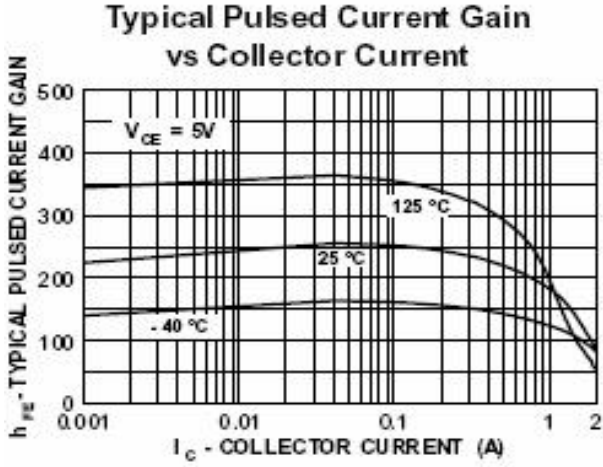
| Symbol | Parameter | Value | Units |
|-----------|-------------------------------|---------|--------------------|
| V_{CB0} | Collector-Base Voltage | 50 | V |
| V_{CE0} | Collector-Emitter Voltage | 45 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current -Continuous | 0.5 | A |
| P_C | Collector Power Dissipation | 0.3 | W |
| T_j | Junction Temperature | 150 | $^{\circ}\text{C}$ |
| T_{stg} | Storage Temperature | -55-150 | $^{\circ}\text{C}$ |

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|--------------------------------------|---------------|---|-----|-----|---------------|
| Collector-base breakdown voltage | V_{CB0} | $I_C=10\mu\text{A}$, $I_E=0$ | 50 | | V |
| Collector-emitter breakdown voltage | V_{CE0} | $I_C=10\text{mA}$, $I_B=0$ | 45 | | V |
| Emitter-base breakdown voltage | V_{EBO} | $I_E=1\mu\text{A}$, $I_C=0$ | 5 | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=45\text{V}$, $I_E=0$ | | 0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=4\text{V}$, $I_C=0$ | | 0.1 | μA |
| DC current gain | $h_{FE(1)}$ | $V_{CE}=1\text{V}$, $I_C=100\text{mA}$ | 160 | 400 | |
| | $h_{FE(2)}$ | $V_{CE}=1\text{V}$, $I_C=500\text{mA}$ | 40 | | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=500\text{mA}$, $I_B=50\text{mA}$ | | 0.7 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_C=500\text{mA}$, $I_B=50\text{mA}$ | | 1.2 | V |
| Base-emitter voltage | V_{BE} | $V_{CE}=1\text{V}$, $I_C=500\text{mA}$ | | 1.2 | V |
| Collector capacitance | C_{ob} | $V_{CB}=10\text{V}$, $f=1\text{MHz}$ | | 10 | pF |
| Transition frequency | f_T | $V_{CE}=5\text{V}$, $I_C=10\text{mA}$ $f=100\text{MHz}$ | 100 | | MHz |

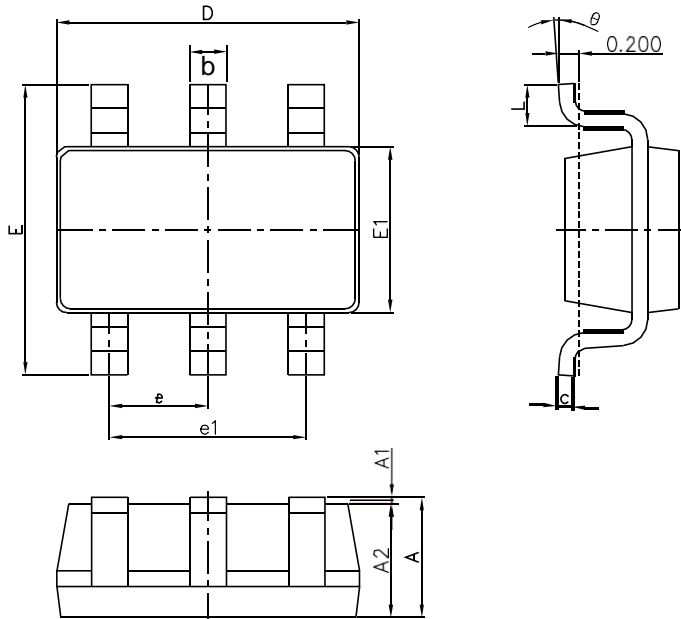
BC817DS

Typical Characteristics



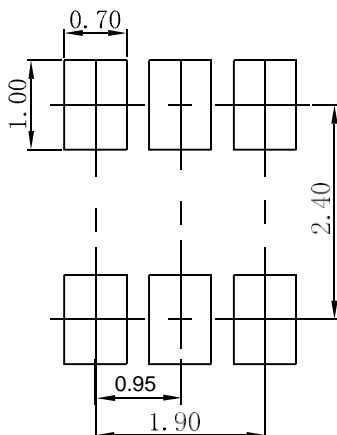
BC817DS

SOT-23-6L Package Outline Dimensions



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E1 | 1.500 | 1.700 | 0.059 | 0.067 |
| E | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |

SOT-23-6L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.